<u>TOSHIBA</u>

TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

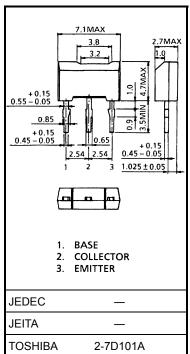
2SA1431

Strobe Flash Applications Medium Power Amplifier Applications

- High DC current gain and excellent hFE linearity
 : hFE(1) = 100 to 320 (VCE = -2 V, IC = -0.5 A)
 : hFE(2) = 70 (min) (VCE = -2 V, IC = -4 A)
- Low saturation voltage: $V_{CE (sat)} = -1.0 V (max)$ (IC = -4 A, IB = -0.1 A)

Absolute Maximum Ratings (Ta = 25°C)

| Characteristics | | Symbol | Rating | Unit | |
|-----------------------------|--------------------|------------------|------------|------|--|
| Collector-base voltage | | V _{CBO} | -35 | V | |
| Collector-emitter voltage | | V _{CEO} | -20 | V | |
| Emitter-base voltage | | V _{EBO} | -8 | V | |
| Collector current | DC | Ι _C | -5 | A | |
| | Pulsed (Note 1) | I _{CP} | -8 | | |
| Base current | | Ι _Β | -0.5 | А | |
| Collector power dissipation | | P _C | 1000 | mW | |
| Junction temperature | | Tj | 150 | °C | |
| Storage temperature range | | T _{stg} | -55 to 150 | °C | |



Weight: 0.2 g (typ.)

Note 1: Pulse width = 10 ms (max), duty cycle = 30% (max)

Note 2: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

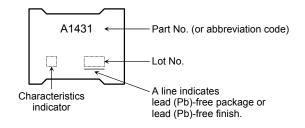
Unit: mm

Electrical Characteristics (Ta = 25°C)

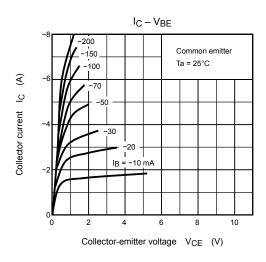
| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------------|---------------------------------|--|-----|------|------|------|
| Collector cut-off current | I _{CBO} | $V_{CB} = -35 V, I_E = 0$ | — | _ | -100 | nA |
| Emitter cut-off current | I _{EBO} | $V_{EB} = -8 V, I_C = 0$ | _ | _ | -100 | nA |
| Collector-emitter breakdown voltage | V (BR) CEO | I _C = -10 mA, I _B = 0 | -20 | — | _ | V |
| Emitter-base breakdown voltage | V (BR) EBO | $I_{\rm E} = -1 {\rm mA}, I_{\rm C} = 0$ | -8 | _ | _ | V |
| DC current gain | h _{FE (1)} (Note 3) | V _{CE} = -2 V, I _C = -0.5 A | 100 | _ | 320 | |
| | h _{FE (2)} | V _{CE} = -2 V, I _C = -4 A | 70 | _ | _ | |
| Collector-emitter saturation voltage | V _{CE (sat)} | I _C = -4 A, I _B = -0.1 A | _ | _ | -1.0 | V |
| Base-emitter voltage | V _{BE} | V _{CE} = -2 V, I _C = -4 A | _ | _ | -1.5 | V |
| Transition frequency | fT | V _{CE} = -2 V, I _C = -0.5 A | — | 170 | _ | MHz |
| Collector output capacitance | C _{ob} | V _{CB} = −10 V, I _E = 0, f = 1 MHz | _ | 62 | _ | pF |

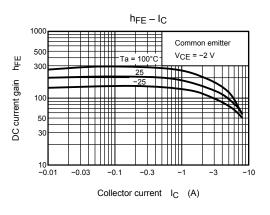
Note 3: hFE (1) classification O: 100 to 200, Y: 160 to 320

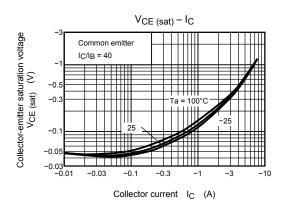
Marking

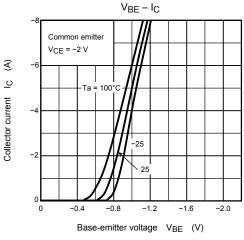


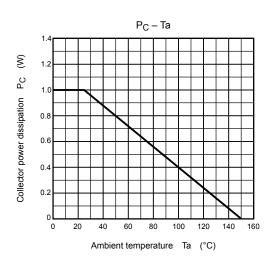
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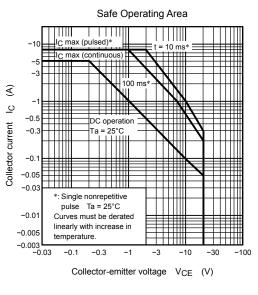












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